

GenX3[™] 300V IGBT

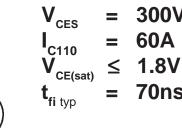
IXGH60N30C3

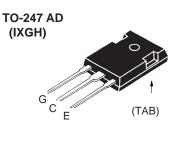
High Speed IGBTs for 50-150kHz switching



			0 E		
Symbol	Test Conditions	Maximum Ratings			
V _{CES}	$T_{J} = 25^{\circ}C$ to $150^{\circ}C$	300	V		
V _{cgr}	$T_{J} = 25^{\circ}C$ to 150°C, $R_{GE} = 1M\Omega$	300	V		
V _{ges}	Continuous	±20	V		
V _{gem}	Transient	±30	V		
I _{C25}	$T_{c} = 25^{\circ}C$ (Limited by leads)	75	A		
I _{C110}	$T_c = 110^{\circ}C$ (chip capability)	60	А		
I _{CM}	$T_c = 25^{\circ}C$, 1ms	420	A		
I _A	$T_c = 25^{\circ}C$	60	А		
E _{AS}	$T_c = 25^{\circ}C$	400	mJ		
SSOA (RBSOA)	V_{GE} = 15V, T_{VJ} = 125°C, R_{G} = 5 Ω Clamped inductive load @ \leq 300V	I _{CM} = 170	A		
P _c	T _c = 25°C	300	W		
T,		-55 +150	°C		
Т _{јм}		150	°C		
T _{stg}		-55 +150	°C		
T _l T _{sold}	Maximum lead temperature for soldering 1.6 mm (0.062 in.) from case for 10s	300 260	°C ℃		
M _d	Mounting torque (TO-247)	1.13/10	Nm/lb.in.		
Weight		6	g		

Symbol	Test Conditions	Characteristic Values $(T_J = 25^{\circ}C, \text{ unless otherwise specified})$				
		Min.	Тур.	Max.		
BV _{CES}	$I_{c} = 250 \mu A, V_{ce} = 0 V$	300			V	
	$ \begin{array}{ll} I_{\mathrm{C}} &= 250 \mu A, \ V_{\mathrm{GE}} = 0V \\ I_{\mathrm{C}} &= 250 \mu A, \ V_{\mathrm{CE}} = V_{\mathrm{GE}} \end{array} $	2.5		5.0	V	
I _{ces}	$V_{CE} = V_{CES}$			30	μA	
	$\begin{array}{l} V_{\rm CE} &= V_{\rm CES} \\ V_{\rm GE} &= 0 V \end{array}$	$T_J = 125^{\circ}C$		750	μΑ	
GES	$V_{_{CE}}$ = 0V, $V_{_{GE}}$ = ± 20V			±100	nA	
V _{CE(sat)}	I _c = 60A, V _{GE} = 15V		1.55	1.8	V	
	G GE	T _J = 125°C	1.60		V	





G = Gate E = Emitter

C = CollectorTAB = Collector

300V

60A

70ns

Features

- High Frequency IGBT
- Square RBSOA
- High avalanche capability
- Drive simplicity with MOS Gate Turn-On
- High current handling capability

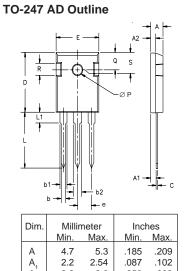
Applications

- PFC Circuits
- PDP Systems
- Switched-mode and resonant-mode converters and inverters
- SMPS
- AC motor speed control
- DC servo and robot drives
- DC choppers

Symbol Test Conditions

IXGH60N30C3

SymbolTest Conditions $(T_j = 25^{\circ}C, unless otherwise specified)$	Min.	Characteristic Values Typ. Max.		
	28	46	S	
$\left.\begin{array}{c} \textbf{C}_{ies} \\ \textbf{C}_{oes} \\ \textbf{C}_{res} \end{array}\right\} V_{CE} = 25V, V_{GE} = 0V, f = 1MHz$		3800 240 63	pF pF pF	
$ \begin{array}{c} \mathbf{Q}_{g} \\ \mathbf{Q}_{ge} \\ \mathbf{Q}_{gc} \end{array} \end{array} \right\} \ \ I_{C} = I_{C110}, \ \ V_{GE} = 15V, \ \ V_{CE} = 0.5 \bullet V_{CES} $		101 21 37	nC nC nC	
$ \begin{array}{c} \mathbf{t}_{d(on)} \\ \mathbf{t}_{ri} \\ \mathbf{E}_{on} \\ \mathbf{t}_{d(off)} \\ \mathbf{t}_{fi} \\ \mathbf{E}_{off} \end{array} \end{array} \right\} \begin{array}{c} \mathbf{Inductive \ Load, \ T_{J} = 25^{\circ}C} \\ \mathbf{I}_{C} = 0.5 \bullet \mathbf{I}_{C110}, \ \mathbf{V}_{GE} = 15 \mathbf{V} \\ \mathbf{V}_{CE} = 200 \mathbf{V}, \ \mathbf{R}_{G} = 5\Omega \end{array} $		23 28 0.15 108 68 0.30	ns ns mJ 160 ns ns 0.55 mJ	
$ \begin{array}{c} \mathbf{t}_{d(on)} \\ \mathbf{t}_{ri} \\ \mathbf{E}_{on} \\ \mathbf{t}_{d(off)} \\ \mathbf{t}_{fi} \\ \mathbf{E}_{off} \end{array} \end{array} \right\} \begin{array}{c} \mathbf{Inductive \ Load, \ T_{J} = 125^{\circ}C} \\ \mathbf{I}_{C} = 0.5 \bullet \mathbf{I}_{C110}, \ V_{GE} = 15V \\ V_{CE} = 200V, \ R_{G} = 5\Omega \end{array} $		22 28 0.26 120 101 0.40	ns ns mJ ns ns mJ	
R _{thJC} R _{thCK}		0.21	0.42 °C/W °C/W	



A A₂ 2.2 2.6 .059 .098 b 1.0 1.4 .040 .055 b, 1.65 2.13 .065 .084 b, 2.87 3.12 .113 .123 C .8 .016 .031 .4 D E 20.80 21.46 .819 .845 15.75 16.26 .610 .640 e L 5.20 5.72 0.205 0.225 19.81 20.32 .780 .800 L1 4.50 .177 ØP 3.55 3.65 .140 .144 Q 5.89 6.40 0.232 0.252 R 4.32 5.49 .170 .216 S 6.15 BSC 242 BSC

ADVANCE TECHNICAL INFORMATION

The product presented herein is under development. The Technical Specifications offered are derived from a subjective evaluation of the design, based upon prior knowledge and experience, and constitute a "considered reflection" of the anticipated result. IXYS reserves the right to change limits, test conditions, and dimensions without notice.

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IXYS MOSFETs and IGBTs are covered	4,835,592	4,931,844	5,049,961	5,237,481	6,162,665	6,404,065 B1	6,683,344	6,727,585	7,005,734 B2	7,157,338B2
by one or moreof the following U.S. patents:						- , ,	6,710,405 B2	- / /	/	
	4,881,106	5,034,796	5,187,117	5,486,715	6,306,728 B1	6,583,505	6,710,463	6,771,478 B2	7,071,537	



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